

# Ryoichi Suzuki

## List of Publications by Year in descending order

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#	ARTICLE	IF	CITATIONS
1	Free-Volume Depth Profile of Polymeric Membranes Studied by Positron Annihilation Spectroscopy: Layer Structure from Interfacial Polymerization. <i>Macromolecules</i> , 2007, 40, 7542-7557.	4.8	249
2	Slow Positron Pulsing System for Variable Energy Positron Lifetime Spectroscopy. <i>Japanese Journal of Applied Physics</i> , 1991, 30, L532-L534.	1.5	183
3	Production and recovery of defects in phosphorus-implanted ZnO. <i>Journal of Applied Physics</i> , 2005, 97, 013528.	2.5	128
4	Probing the internal structure of reverse osmosis membranes by positron annihilation spectroscopy: Gaining more insight into the transport of water and small solutes. <i>Journal of Membrane Science</i> , 2015, 486, 106-118.	8.2	108
5	Pore Size Determination of TEMPO-Oxidized Cellulose Nanofibril Films by Positron Annihilation Lifetime Spectroscopy. <i>Biomacromolecules</i> , 2011, 12, 4057-4062.	5.4	105
6	A variable energy positron annihilation lifetime spectroscopy study of physical aging in thin glassy polymer films. <i>Polymer</i> , 2009, 50, 6149-6156.	3.8	97
7	Evolution of voids in Al <sup>+</sup> -implanted ZnO probed by a slow positron beam. <i>Physical Review B</i> , 2004, 69, .	3.2	93
8	Study of defects in GaN grown by the two-flow metalorganic chemical vapor deposition technique using monoenergetic positron beams. <i>Journal of Applied Physics</i> , 2001, 90, 181-186.	2.5	92
9	Microvoid formation in hydrogen-implanted ZnO probed by a slow positron beam. <i>Physical Review B</i> , 2005, 71, .	3.2	89
10	Positronium reemission yield from mesostructured silica films. <i>Applied Physics Letters</i> , 2008, 92, .	3.3	70
11	Correlation Study between Free-Volume Holes and Molecular Separations of Composite Membranes for Reverse Osmosis Processes by Means of Variable-Energy Positron Annihilation Techniques. <i>Journal of Physical Chemistry C</i> , 2011, 115, 18055-18060.	3.1	69
12	Free-volume hole model for positronium formation in polymers: surface studies. <i>Journal of Physics Condensed Matter</i> , 1998, 10, 10429-10442.	1.8	63
13	First lasing of the NIIJ-IV storage-ring free-electron laser. <i>Nuclear Instruments and Methods in Physics Research, Section A: Accelerators, Spectrometers, Detectors and Associated Equipment</i> , 1993, 331, 27-33.	1.6	59
14	A positron lifetime spectroscopy apparatus for surface and near-surface positronium experiments. <i>Radiation Physics and Chemistry</i> , 2000, 58, 603-606.	2.8	59
15	Nanoporous structure of sputter-deposited silicon oxide films characterized by positronium annihilation spectroscopy. <i>Journal of Applied Physics</i> , 2002, 91, 1704-1706.	2.5	57
16	Stretching of slow positron pulses generated with an electron linac. <i>Applied Physics A: Solids and Surfaces</i> , 1990, 51, 146-150.	1.4	55
17	Brightness enhancement method for a high-intensity positron beam produced by an electron accelerator. <i>Journal of Applied Physics</i> , 2008, 103, .	2.5	53
18	Native cation vacancies in Si-doped AlGaIn studied by monoenergetic positron beams. <i>Journal of Applied Physics</i> , 2012, 111, .	2.5	53

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19	Point defects in group-III nitride semiconductors studied by positron annihilation. <i>Journal of Crystal Growth</i> , 2009, 311, 3075-3079.	1.5	51
20	Evidence for pore surface dependent positronium thermalization in mesoporous silica/hybrid silica films. <i>Physical Review B</i> , 2007, 75, .	3.2	49
21	Development of positron annihilation spectroscopy to test accelerated weathering of protective polymer coatings. <i>Radiation Physics and Chemistry</i> , 2000, 58, 639-644.	2.8	48
22	Characterization of pore size distribution (PSD) in cellulose triacetate (CTA) and polyamide (PA) thin active layers by positron annihilation lifetime spectroscopy (PALS) and fractional rejection (FR) method. <i>Journal of Membrane Science</i> , 2017, 527, 143-151.	8.2	48
23	Linearly polarized photons from Compton backscattering of laser light for nuclear resonance fluorescence experiments. <i>Nuclear Instruments and Methods in Physics Research, Section A: Accelerators, Spectrometers, Detectors and Associated Equipment</i> , 1994, 353, 384-388.	1.6	45
24	Depth Profile of Free Volume in a Mixture and Copolymers of Poly(N-vinyl-pyrrolidone) and Poly(ethylene glycol) Studied by Positron Annihilation Spectroscopy. <i>Biomacromolecules</i> , 2003, 4, 1856-1864.	5.4	45
25	Characterization of Hydrogenated Amorphous Silicon Films by a Pulsed Positron Beam. <i>Japanese Journal of Applied Physics</i> , 1991, 30, 2438-2441.	1.5	44
26	Vacancy Clusters on Surfaces of Au Nanoparticles Embedded in MgO. <i>Physical Review Letters</i> , 1999, 83, 4586-4589.	7.8	44
27	Rejection of small and uncharged chemicals of emerging concern by reverse osmosis membranes: The role of free volume space within the active skin layer. <i>Separation and Purification Technology</i> , 2013, 116, 426-432.	7.9	44
28	Possible presence of hydrophilic SO <sub>3</sub> H nanoclusters on the surface of dry ultrathin Nafion® films: a positron annihilation study. <i>Physical Chemistry Chemical Physics</i> , 2013, 15, 1518-1525.	2.8	44
29	Characterization of free volume and density gradients of polystyrene surfaces by low-energy positron lifetime measurements. <i>Polymer</i> , 2004, 45, 4533-4539.	3.8	43
30	Rapid three-dimensional imaging of defect distributions using a high-intensity positron microbeam. <i>Applied Physics Letters</i> , 2009, 94, 194104.	3.3	43
31	Positron-annihilation studies of stable Al-based icosahedral quasicrystals. <i>Physical Review B</i> , 1999, 59, 6712-6716.	3.2	40
32	Degradation of Polymer Coating Systems Studied by Positron Annihilation Spectroscopy. 3. Wavelength Dependence of UV Irradiation Effect. <i>Macromolecules</i> , 1999, 32, 5925-5933.	4.8	40
33	Role of pore morphology in positronium diffusion in mesoporous silica thin films and in positronium emission from the surfaces. <i>Physical Review B</i> , 2012, 86, .	3.2	40
34	Positron Study of Electron Momentum Density and Fermi Surface in Titanium and Zirconium. <i>Journal of the Physical Society of Japan</i> , 1989, 58, 3251-3263.	1.6	38
35	Annealing properties of vacancy-type defects in ion-implanted GaN studied by monoenergetic positron beams. <i>Journal of Applied Physics</i> , 2007, 102, 084505.	2.5	38
36	Positronium formation in SiO <sub>2</sub> films grown on Si substrates studied by monoenergetic positron beams. <i>Journal of Applied Physics</i> , 1994, 75, 3822-3828.	2.5	35

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37	Free volumes and holes near the polymer surface studied by positron annihilation. Applied Surface Science, 1999, 149, 116-124.	6.1	35
38	Nanoporous structure of methyl-silsesquioxane films using monoenergetic positron beams. Journal of Applied Physics, 2001, 90, 2498-2503.	2.5	35
39	Positronium annihilation and pore surface chemistry in mesoporous silica films. Applied Physics Letters, 2007, 91, .	3.3	34
40	Free volume behavior in spincoated thin film of polystyrene by energy variable positron annihilation lifetime spectroscopy. Polymer, 2009, 50, 3343-3346.	3.8	34
41	Ion-beam-induced recrystallization in Si(100) studied with slow positron annihilation and Rutherford backscattering and channeling. Physical Review Letters, 1993, 70, 45-48.	7.8	33
42	Vacancy-type defects in BaTiO <sub>3</sub> /SrTiO <sub>3</sub> structures probed by monoenergetic positron beams. Journal of Applied Physics, 2002, 91, 5307-5312.	2.5	33
43	Annealing Properties of Defects in B <sup>+</sup> - and F <sup>+</sup> -Implanted Si Studied Using Monoenergetic Positron Beams. Japanese Journal of Applied Physics, 1997, 36, 2571-2580.	1.5	32
44	Porogen Approach for the Fabrication of Plasma-Polymerized Nanoporous Polysiloxane Films. Journal of Physical Chemistry B, 2006, 110, 20172-20176.	2.6	31
45	Anion vacancies in CuInSe <sub>2</sub> . Thin Solid Films, 2001, 387, 129-134.	1.8	30
46	Mechanism of enhanced positronium formation in low-temperature polymers. Journal of Chemical Physics, 2005, 122, 214907.	3.0	30
47	Free-volume hole properties near the surface of polymers obtained from slow positron annihilation spectroscopy. Applied Surface Science, 1997, 116, 251-255.	6.1	29
48	Vacancy defects in solid-phase epitaxially grown layers of self-implanted Si. Applied Physics Letters, 1999, 74, 997-999.	3.3	29
49	Pore Characteristics of Low-Dielectric-Constant Films Grown by Plasma-Enhanced Chemical Vapor Deposition Studied by Positron Annihilation Lifetime Spectroscopy. Japanese Journal of Applied Physics, 2001, 40, L414-L416.	1.5	29
50	Quantum Antidot Formation and Correlation to Optical Shift of Gold Nanoparticles Embedded in MgO. Physical Review Letters, 2002, 88, 175502.	7.8	29
51	Interaction of nitrogen with vacancy defects in N <sup>+</sup> -implanted ZnO studied using a slow positron beam. Applied Physics Letters, 2005, 87, 091910.	3.3	29
52	Free-volume distribution and glass transition of nano-scale polymeric films. Radiation Physics and Chemistry, 2007, 76, 172-179.	2.8	29
53	Generation of an intense pulsed positron beam for positron lifetime and TOF experiments. Applied Surface Science, 1995, 85, 87-91.	6.1	28
54	Investigation of Positron Moderator Materials for Electron-Linac-Based Slow Positron Beamlines. Japanese Journal of Applied Physics, 1998, 37, 4636-4643.	1.5	28

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55	Properties of Low-k Copper Barrier SiOCH Film Deposited by PECVD Using Hexamethyldisiloxane and N <sub>2</sub> O. Journal of the Electrochemical Society, 2003, 150, F83.	2.9	28
56	Free Volume and Density Gradients of Amorphous Polymer Surfaces As Determined by Use of a Pulsed Low-Energy Positron Lifetime Beam and PVT Data. Macromolecules, 2004, 37, 4201-4210.	4.8	28
57	Positron-lifetime study on porous silicon with a monoenergetic pulsed positron beam. Physical Review B, 1994, 49, 17484-17487.	3.2	27
58	Identification of open-volume defects in disordered and amorphized Si: A depth-resolved positron annihilation study. Physical Review B, 2001, 63, .	3.2	26
59	Positron annihilation in SiO <sub>2</sub> -Si studied by a pulsed slow positron beam. Applied Surface Science, 2002, 194, 89-96.	6.1	26
60	Positronium time-of-flight measurements of porous low-k films. Applied Physics Letters, 2003, 83, 4966-4968.	3.3	26
61	Positron Annihilation Spectroscopy on Nitride-Based Semiconductors. Japanese Journal of Applied Physics, 2013, 52, 08J02.	1.5	26
62	<i>In-situ</i> characterization of free-volume holes in polymer thin films under controlled humidity conditions with an atmospheric positron probe microanalyzer. Applied Physics Letters, 2012, 101, .	3.3	25
63	Positron Annihilation in Cardo-Based Polymer Membranes. Journal of Physical Chemistry B, 2014, 118, 6007-6014.	2.6	25
64	Lasing in visible of a storage-ring free electron laser at ETL. Nuclear Instruments and Methods in Physics Research, Section A: Accelerators, Spectrometers, Detectors and Associated Equipment, 1991, 309, 343-347.	1.6	24
65	Defects introduced into electroplated Cu films during room-temperature recrystallization probed by a monoenergetic positron beam. Journal of Applied Physics, 2005, 98, 043504.	2.5	24
66	Characterization of Separation-by-Implanted-Oxygen Wafers with Monoenergetic Positron Beams. Japanese Journal of Applied Physics, 1993, 32, 3682-3686.	1.5	23
67	Effects of Recoil-Implanted Oxygen on Depth Profiles of Defects and Annealing Processes in P <sup>+</sup> -Implanted Si Studied Using Monoenergetic Positron Beams. Japanese Journal of Applied Physics, 1996, 35, 2000-2007.	1.5	23
68	Dependence of porosity in methyl-silsesquioxane thin films on molecular weight of sacrificial triblock copolymer. Chemical Physics Letters, 2002, 364, 309-313.	2.6	23
69	Tunable pores in mesoporous silica films studied using a pulsed slow positron beam. Radiation Physics and Chemistry, 2007, 76, 204-208.	2.8	23
70	Hydrogen-terminated defects in ion-implanted silicon probed by monoenergetic positron beams. Journal of Applied Physics, 2003, 93, 3228-3233.	2.5	22
71	Characterization of HfSiON gate dielectrics using monoenergetic positron beams. Journal of Applied Physics, 2006, 99, 054507.	2.5	22
72	Application of positron beams to the study of positronium-forming solids. Applied Surface Science, 2008, 255, 174-178.	6.1	22

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73	Effect of UV anneal on plasma CVD low-k film. Journal of Non-Crystalline Solids, 2008, 354, 2973-2982.	3.1	22
74	Tailoring the Chain Packing in Ultrathin Polyelectrolyte Films Formed by Sequential Adsorption: Nanoscale Probing by Positron Annihilation Spectroscopy. Journal of the American Chemical Society, 2012, 134, 19808-19819.	13.7	22
75	Degradation of polymer coating systems studied by positron annihilation spectroscopy. IV. Oxygen effect of UV irradiation. Journal of Polymer Science, Part B: Polymer Physics, 2001, 39, 2035-2047.	2.1	21
76	A positron annihilation lifetime measurement system with an intense positron microbeam. Radiation Physics and Chemistry, 2009, 78, 1096-1098.	2.8	21
77	Three-dimensional positron-electron momentum distribution in single-crystal graphite. Physical Review B, 1990, 42, 11583-11586.	3.2	20
78	Annealing properties of defects during Si-on-insulator fabrication by low-dose oxygen implantation studied by monoenergetic positron beams. Journal of Applied Physics, 2000, 87, 1659-1665.	2.5	20
79	Characterization of low temperature grown Si layer for SiGe pseudo-substrates by positron annihilation spectroscopy. Journal of Crystal Growth, 2001, 227-228, 761-765.	1.5	20
80	Porosity in porous methyl-silsesquioxane (MSQ) films. Applied Surface Science, 2002, 194, 189-194.	6.1	20
81	Annealing properties of open volumes in HfSiO <sub>x</sub> and HfAlO <sub>x</sub> gate dielectrics studied using monoenergetic positron beams. Journal of Applied Physics, 2005, 98, 023506.	2.5	20
82	Structure of SiO <sub>2</sub> /Si interface probed by positron annihilation spectroscopy. Physical Review B, 2006, 73, .	3.2	20
83	Variable-energy positron annihilation study of subnanopores in SiOCH-based PECVD films. Radiation Physics and Chemistry, 2007, 76, 213-216.	2.8	20
84	Mesoporous silica films with varying porous volume fraction: Direct correlation between ortho-positronium annihilation decay and escape yield into vacuum. Applied Physics Letters, 2009, 95, 124103.	3.3	20
85	Structural Defects and Positronium Formation in 40 keV B <sup>+</sup> -Implanted Polymethylmethacrylate. Journal of Physical Chemistry B, 2014, 118, 4194-4200.	2.6	20
86	Characterization of Diamond Films by Means of a Pulsed Positron Beam. Japanese Journal of Applied Physics, 1992, 31, 2237-2240.	1.5	19
87	SiO <sub>2</sub> films deposited on Si substrates studied by monoenergetic positron beams. Journal of Applied Physics, 1994, 75, 216-222.	2.5	19
88	Degradation and restoration of dielectric-coated cavity mirrors in the NII-IV FEL. Nuclear Instruments and Methods in Physics Research, Section A: Accelerators, Spectrometers, Detectors and Associated Equipment, 1995, 358, 392-395.	1.6	19
89	Moderation of Positrons Generated by an Electron Linac. Materials Science Forum, 1997, 255-257, 114-118.	0.3	19
90	Open spaces in the subsurface region of polyethylene probed by monoenergetic positron beams. Journal of Polymer Science, Part B: Polymer Physics, 1998, 36, 2597-2605.	2.1	19

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91	Positron re-emission from tungsten surfaces. <i>Applied Surface Science</i> , 1999, 149, 66-70.	6.1	19
92	Study of mesoporous silica films by positron annihilation based on a slow positron beam: Effects of preparation conditions on pore size and open porosity. <i>Chemical Physics</i> , 2007, 331, 213-218.	1.9	19
93	Slow positron beam study of corrosion-related defects in pure iron. <i>Applied Surface Science</i> , 2006, 252, 3274-3277.	6.1	18
94	Vacancy-Type Defects in Ion-Implanted Diamonds Probed by Monoenergetic Positron Beams. <i>Japanese Journal of Applied Physics</i> , 1995, 34, 1772-1777.	1.5	17
95	Positron studies of polymeric coatings. <i>Radiation Physics and Chemistry</i> , 2003, 68, 395-402.	2.8	17
96	Saturation of cavity-mirror degradation in the UV FEL. <i>Nuclear Instruments and Methods in Physics Research, Section A: Accelerators, Spectrometers, Detectors and Associated Equipment</i> , 1997, 393, 44-49.	1.6	16
97	Annealing Properties of Defects in Ion-Implanted 3C-SiC Studied Using Monoenergetic Positron Beams. <i>Japanese Journal of Applied Physics</i> , 1997, 36, 6650-6660.	1.5	15
98	Characterization of H-related defects in H-implanted Si with slow positrons. <i>Applied Surface Science</i> , 1999, 149, 188-192.	6.1	15
99	Crystallization of an amorphous layer in P <sup>+</sup> -implanted 6H-SiC studied by monoenergetic positron beams. <i>Journal of Applied Physics</i> , 2000, 87, 4119-4125.	2.5	15
100	Low-kSiOCH Film Deposited by Plasma-Enhanced Chemical Vapor Deposition Using Hexamethyldisiloxane and Water Vapor. <i>Japanese Journal of Applied Physics</i> , 2005, 44, 3879-3884.	1.5	15
101	Vacancy-type defects in In <sub>x</sub> Ga <sub>1-x</sub> N grown on GaN templates probed using monoenergetic positron beams. <i>Journal of Applied Physics</i> , 2013, 114, .	2.5	15
102	Performance evaluation of polyamide TFC membranes: Effects of free volume properties on boron transport. <i>Desalination</i> , 2018, 432, 104-114.	8.2	15
103	Durability and Free Volume in Polymeric Coatings Studied by Positron Annihilation Spectroscopy. <i>Materials Science Forum</i> , 2004, 445-446, 274-276.	0.3	14
104	Structural defects in SiO <sub>2</sub> /SiC interface probed by a slow positron beam. <i>Applied Surface Science</i> , 2005, 244, 322-325.	6.1	14
105	Vacancy-type defects in Si-doped InN grown by plasma-assisted molecular-beam epitaxy probed using monoenergetic positron beams. <i>Journal of Applied Physics</i> , 2005, 97, 043514.	2.5	14
106	Orthopositronium annihilation and emission in mesostructured thin silica and silicalite-1 films. <i>Applied Surface Science</i> , 2008, 255, 187-190.	6.1	14
107	Evolution of pores in mesoporous silica films: Porogen loading effect. <i>Applied Surface Science</i> , 2008, 255, 183-186.	6.1	14
108	Slow Positron Beam Apparatus for Surface and Subsurface Analysis of Samples in Air. <i>Applied Physics Express</i> , 2011, 4, 066701.	2.4	14

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109	(Invited) Point Defect Characterization of Group-III Nitrides by Using Monoenergetic Positron Beams. ECS Transactions, 2014, 61, 19-30.	0.5	14
110	Effect of heat treatment on fouling resistance and the rejection of small and neutral solutes by reverse osmosis membranes. Water Science and Technology: Water Supply, 2015, 15, 510-516.	2.1	14
111	Two-dimensional electron momentum distribution in graphite revealed by means of angular correlation of positron annihilation. Journal of Physics and Chemistry of Solids, 1987, 48, 701-705.	4.0	13
112	Apparatus for positron-annihilation-induced Auger electron spectroscopy with a pulsed positron beam. Applied Surface Science, 1996, 100-101, 297-300.	6.1	13
113	Thermal evolution of defects in H-implanted Si studied by monoenergetic positrons. Physical Review B, 1998, 58, 12559-12562.	3.2	13
114	Characterization of Mg doped GaN by positron annihilation spectroscopy. Journal of Applied Physics, 2002, 92, 1898-1901.	2.5	13
115	Simulations of slow positron production using a low-energy electron accelerator. Review of Scientific Instruments, 2011, 82, 063302.	1.3	13
116	Present status of the NIJI-IV free-electron lasers. Nuclear Instruments and Methods in Physics Research, Section A: Accelerators, Spectrometers, Detectors and Associated Equipment, 1994, 341, ABS3-ABS4.	1.6	12
117	An intense pulsed positron beam. Hyperfine Interactions, 1994, 84, 345-353.	0.5	12
118	Fluorine-Related Defects in BF <sub>2</sub> -Implanted Si Probed by Monoenergetic Positron Beams. Japanese Journal of Applied Physics, 1997, 36, 969-974.	1.5	12
119	Microdefects in Al <sub>2</sub> O <sub>3</sub> films and interfaces revealed by positron lifetime spectroscopy. Applied Physics Letters, 1997, 71, 3165-3167.	3.3	12
120	Electrical and Structural Properties of Al and B Implanted 4H-SiC. Materials Science Forum, 2000, 338-342, 909-912.	0.3	12
121	Deterioration of a polyurethane coating studied by positron annihilation spectroscopy: Correlation with surface properties. Journal of Polymer Science, Part B: Polymer Physics, 2001, 39, 2290-2301.	2.1	12
122	Positronic probe of vacancy defects on surfaces of Au nanoparticles embedded in MgO. Physical Review B, 2001, 64, .	3.2	12
123	Mesoporous low-k hydrogen-silsesquioxane films characterized by positron annihilation and other techniques. Radiation Physics and Chemistry, 2003, 68, 435-437.	2.8	12
124	Ageing-induced enhancement of open porosity of mesoporous silica films studied by positron annihilation spectroscopy. Physics Letters, Section A: General, Atomic and Solid State Physics, 2006, 355, 73-76.	2.1	12
125	Development of Positron Microbeam in AIST. Materials Science Forum, 0, 607, 238-242.	0.3	12
126	Vacancy-type defects induced by grinding of Si wafers studied by monoenergetic positron beams. Journal of Applied Physics, 2014, 116, 134501.	2.5	12

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127	Design of a compact electron accelerator-driven pulsed neutron facility at AIST. Nuclear Instruments and Methods in Physics Research, Section A: Accelerators, Spectrometers, Detectors and Associated Equipment, 2019, 927, 407-418.	1.6	12
128	Lasing in the ultraviolet region with the NII-IV storage-ring free-electron laser. Nuclear Instruments and Methods in Physics Research, Section A: Accelerators, Spectrometers, Detectors and Associated Equipment, 1995, 358, 353-357.	1.6	11
129	Raman Spectroscopy and Positron Lifetime Studies of Structural Relaxation and Defect Evolution in Amorphous Silicon. Japanese Journal of Applied Physics, 1995, 34, 5515-5519.	1.5	11
130	Investigation of Vacancy-Type Defects in P+-Implanted 6H-SiC Using Monoenergetic Positron Beams. Japanese Journal of Applied Physics, 1998, 37, 2422-2429.	1.5	11
131	Positron and positronium annihilation in silica-based thin films studied by a pulsed positron beam. Radiation Physics and Chemistry, 2003, 68, 339-343.	2.8	11
132	Helium ion implantation-induced defects in silicon probed with variable-energy positrons. Physical Review B, 2003, 68, .	3.2	11
133	Copper Barrier Properties of Low Dielectric Constant SiOCNH Film Deposited by Plasma-Enhanced CVD. Journal of the Electrochemical Society, 2004, 151, C56.	2.9	11
134	Development of a Na <sup>22</sup> based pulsed slow positron beam for depth-selective PALS. Physica Status Solidi C: Current Topics in Solid State Physics, 2007, 4, 4020-4022.	0.8	11
135	Vacancy clustering and its dissociation process in electroless deposited copper films studied by monoenergetic positron beams. Journal of Applied Physics, 2012, 111, 104506.	2.5	11
136	On determining the entrance size of cage-like pores in mesoporous silica films by positron annihilation lifetime spectroscopy. Chemical Physics Letters, 2013, 590, 97-100.	2.6	11
137	Free electron laser experiment at ETL. Nuclear Instruments and Methods in Physics Research, Section A: Accelerators, Spectrometers, Detectors and Associated Equipment, 1991, 304, 86-92.	1.6	10
138	Investigation of Near Surface Defects by Variable-Energy Positron Lifetime Spectroscopy. Materials Science Forum, 1992, 105-110, 1459-1462.	0.3	10
139	Positron annihilation in a metal-oxide semiconductor studied by using a pulsed monoenergetic positron beam. Journal of Applied Physics, 1993, 74, 7251-7256.	2.5	10
140	An apparatus for high-resolution positron-annihilation induced Auger-electron spectroscopy using a time-of-flight technique. Applied Surface Science, 1997, 116, 177-180.	6.1	10
141	Application of slow positrons to coating degradation. Radiation Physics and Chemistry, 2000, 58, 645-648.	2.8	10
142	Oxygen-related defects and their annealing behavior in low-dose Separation-by-Implanted OXYgen (SIMOX) wafers studied by slow positron beams. Applied Surface Science, 2002, 194, 112-115.	6.1	10
143	Surface analysis of a well-aligned carbon nanotube film by positron-annihilation induced Auger-electron spectroscopy. Applied Surface Science, 2002, 194, 291-295.	6.1	10
144	Positron emission tomography imaging of musculoskeletal tumors in the shoulder girdle. Journal of Shoulder and Elbow Surgery, 2004, 13, 635-647.	2.6	10

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145	Impact of nitridation on open volumes in HfSiOx studied using monoenergetic positron beams. Applied Physics Letters, 2006, 88, 171912.	3.3	10
146	Characterization of Low-k/Cu Damascene Structures Using Monoenergetic Positron Beams. Japanese Journal of Applied Physics, 2009, 48, 120222.	1.5	10
147	Stable and high current density electron emission using coniferous carbon nano-structured emitter. Diamond and Related Materials, 2015, 55, 41-44.	3.9	10
148	Development of an X-ray tube for irradiation experiments using a field emission electron gun. Nuclear Instruments and Methods in Physics Research, Section A: Accelerators, Spectrometers, Detectors and Associated Equipment, 2016, 807, 41-46.	1.6	10
149	Role of defects during amorphization and relaxation processes in Si. Nuclear Instruments & Methods in Physics Research B, 1995, 106, 198-205.	1.4	9
150	Control of intrinsic defects in molecular beam epitaxy grown CuInSe2. Journal of Crystal Growth, 1999, 201-202, 1061-1064.	1.5	9
151	Open spaces and relaxation processes in the subsurface region of polypropylene probed by monoenergetic positron beams. Journal of Polymer Science, Part B: Polymer Physics, 2000, 38, 101-107.	2.1	9
152	Defects in silicon-on-insulator wafers and their hydrogen interaction studied by monoenergetic positron beams. Journal of Applied Physics, 2002, 91, 6488.	2.5	9
153	Impact of Residual Impurities on Annealing Properties of Vacancies in Electroplated Cu Studied Using Monoenergetic Positron Beams. Japanese Journal of Applied Physics, 2007, 46, L483-L485.	1.5	9
154	Characterization of Metal/High-k Structures Using Monoenergetic Positron Beams. Japanese Journal of Applied Physics, 2007, 46, 3214-3218.	1.5	9
155	Defect profiles in ion-irradiated metal samples by slow positron beams in comparison with simulation profiles. Journal of Physics: Conference Series, 2011, 262, 012029.	0.4	9
156	Free volume change of elongated polyethylene films studied using a positron probe microanalyzer. Applied Physics Letters, 2012, 101, 203108.	3.3	9
157	Characterization of Porous Structures in Advanced Low-k Films with Thin TaN Layers Using Monoenergetic Positron Beams. Japanese Journal of Applied Physics, 2013, 52, 106501.	1.5	9
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